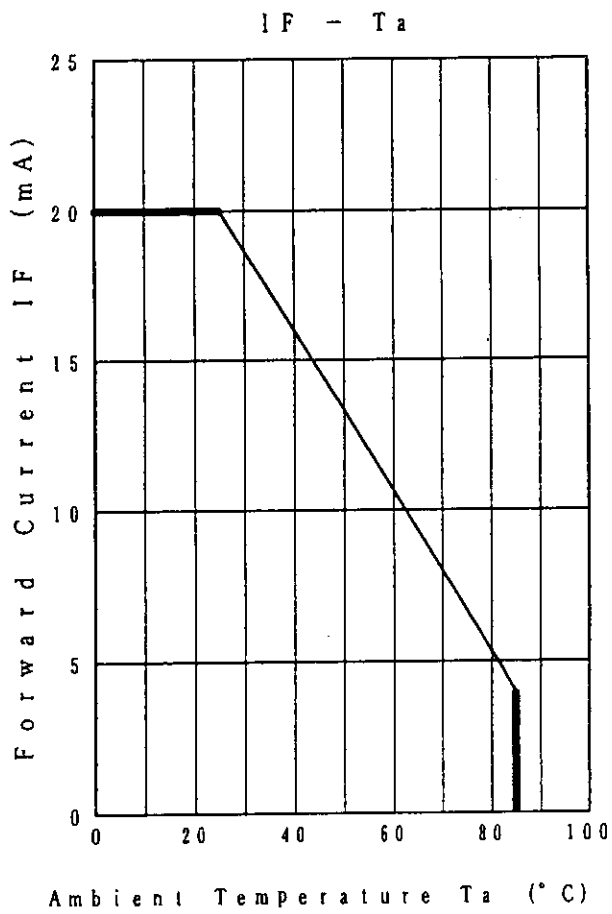
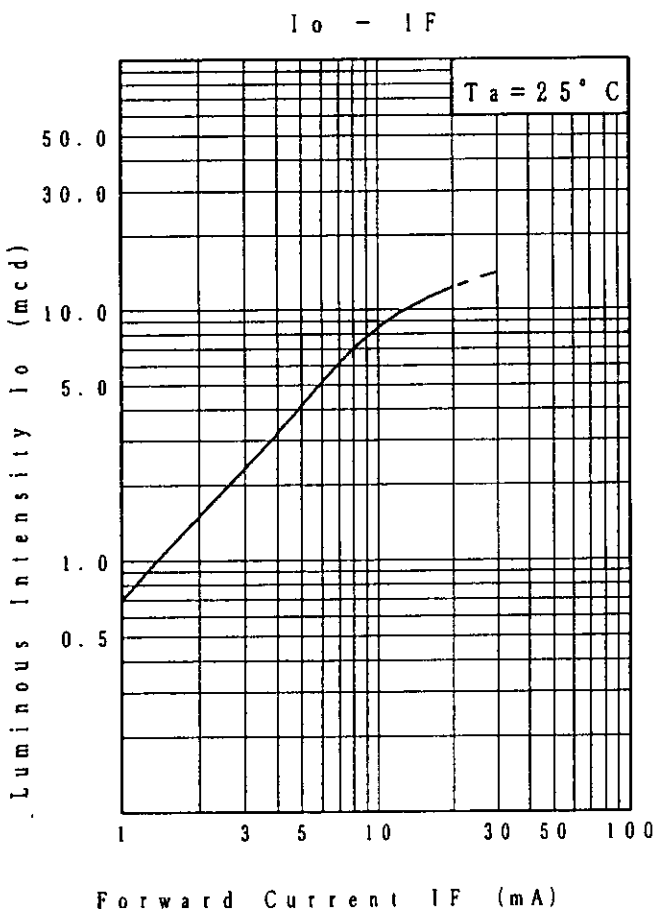
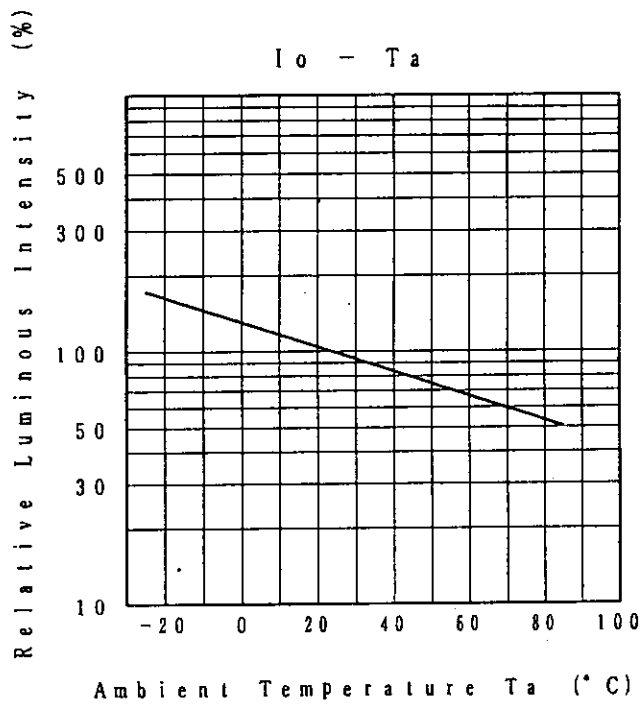
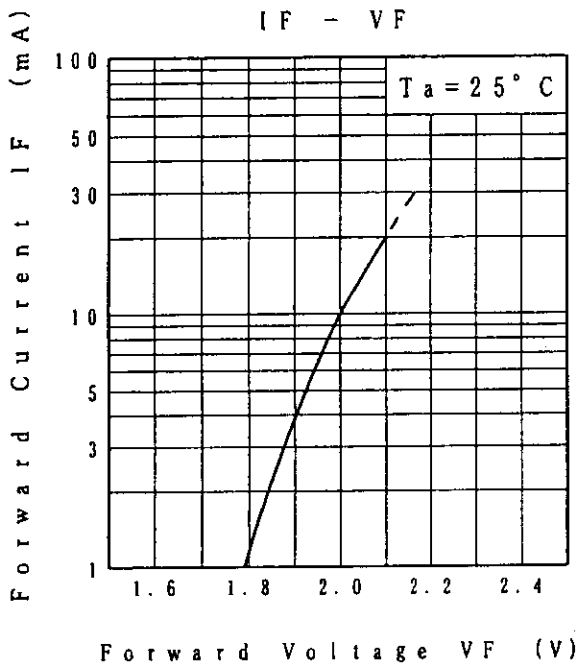


Approved	Checked	Designed	DEVELOPMENT SPECIFICATION					
<i>M. Yamamoto</i>	<i>T. Akeda</i>	<i>T. Tabata</i>	P/N: LNJ406K54UX					
T	Y	P	E	Amber Light Emitting Diode				
APPLICATION			Indicators					
MATERIAL			InGaAlP					
OUTLINE			Attached					
ABSOLUTE MAXIMUM RATINGS			P	※IFP	IFDC	VR	Topr	Tstg
			50	60	20	4	-25~+85	-30~+100
			mW	mA	mA	V	°C	°C
CONDITION			Ta=25±3 °C					
Test Specification								
Item	Symbol	Condition	Typ	Limit		Unit		
				Min	Max			
Forward Voltage	VF	IF=10 mA	2.0		2.3	V		
Reverse Leakage Current	IR	VR= 4 V			100	μA		
Luminous Intensity	IO	IF=10 mA · DC	8.5	3.5		mcd		
Peak Emission Wavelength	λp	IF=10 mA · DC	595			nm		
Spectral Line Half Width	Δλ	IF=10 mA · DC	15			nm		
<p>※ · The Condition of IFP is duty 10 % , Pulse width 1 ms · Please contact the Panasonic local office if you design at low current (below 1.0 mA DC) or pulse current operation and have any questions.</p> <p>NOTE</p> <p>★1 Soldering conditions. Refer to handling note.</p> <p>★2 Care should be taken that soldering is done within 3-days after opening the dry package and reel.</p> <p>★3 Package:Light yellow diffusion type.</p> <p>★4 A InGaAlP LED is sensitive to static electricity and care should be fully taken in handling it. Particularly, when an overvoltage is applied, which exceeds the absolute maximum rating of the InGaAlP LED, its energy damages the LED. Therefore, take utmost proactive measures against static electricity and surge as to building an assembly line and handling the LED halfway the process. (1) Check the entire drive circuit including the power source. For example, a surge current, etc., generated at power-on/off must not exceed the absolute maximum rating of the LED. Also, insert an appropriate protective circuit into the LED drive circuit. (2) Beware of destruction by static electricity in handling the LED. As proactive measures against static electricity, it is effective to earth your body (via 1MΩ), spread conductive mat on the floor, wear semiconductive work uniform and shoes, and use semiconductive containers. Also, be sure to earth the nose of a soldering iron. It is recommended to use an ionizer, etc., in the facility or environment where static electricity may be generated easily.</p>								
Nov. 26. 1996								

Approved <i>K. Yamamoto</i>	Checked <i>T. Ohno</i>	Designed <i>T. Tabata</i>	DEVELOPMENT SPECIFICATION		
			P/N: <u>LNJ406K54UX</u>		



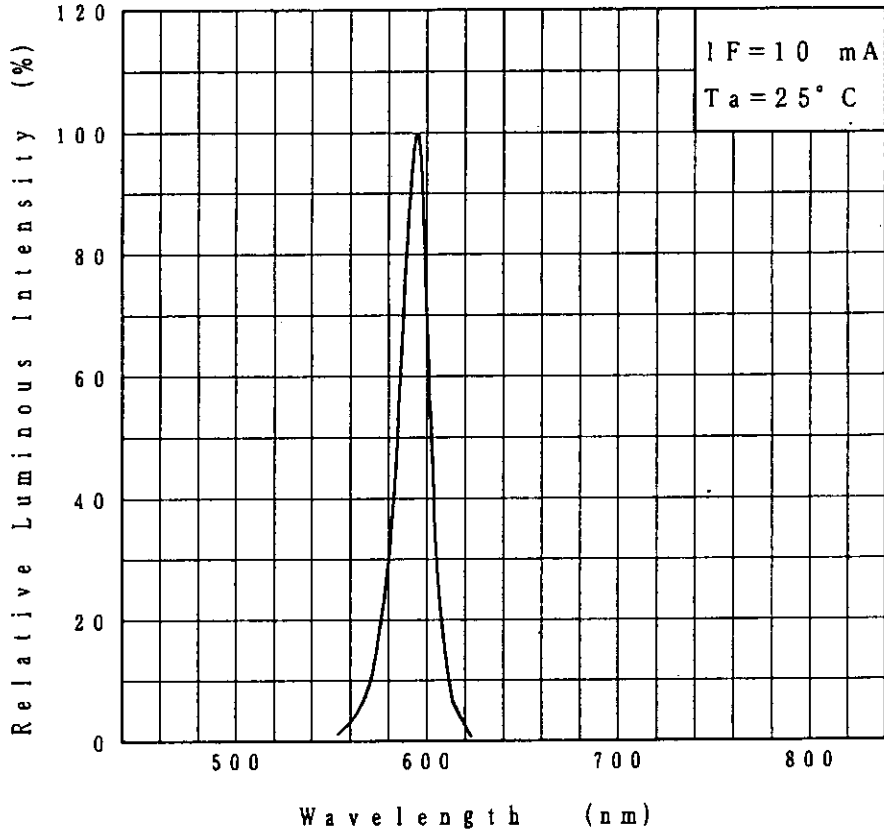
Nov. 27. 1996		
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Approved	Checked	Designed
<i>N. Yamashita</i>	<i>T. Okuda</i>	<i>T. Tabata</i>

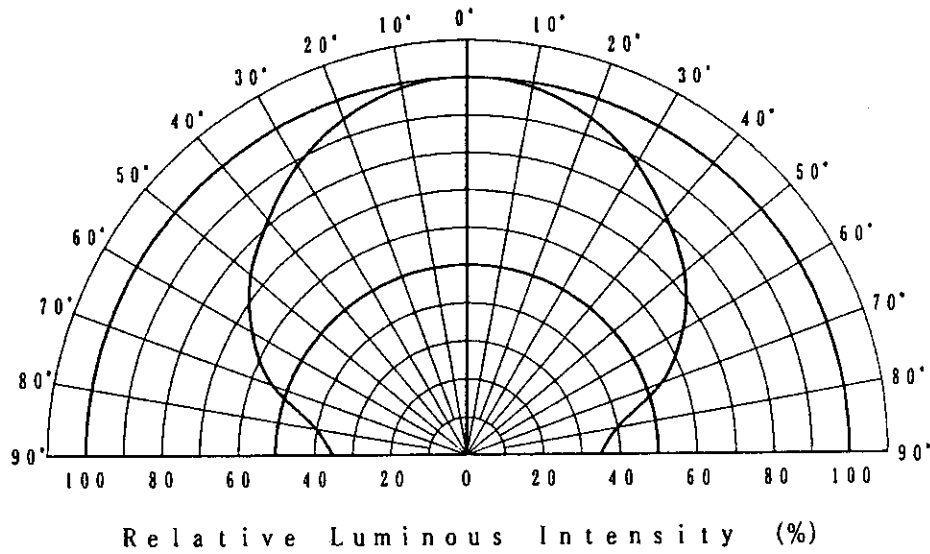
DEVELOPMENT SPECIFICATION

P/N: LNJ406K54UX

Relative Luminous Intensity
Wavelength Characteristics



Directive Characteristics

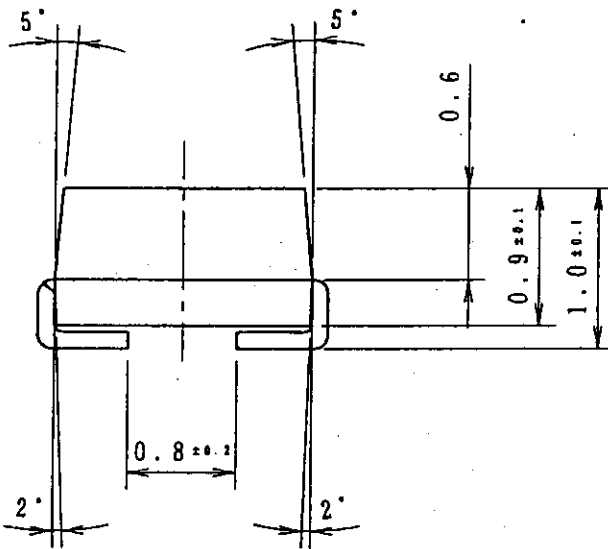
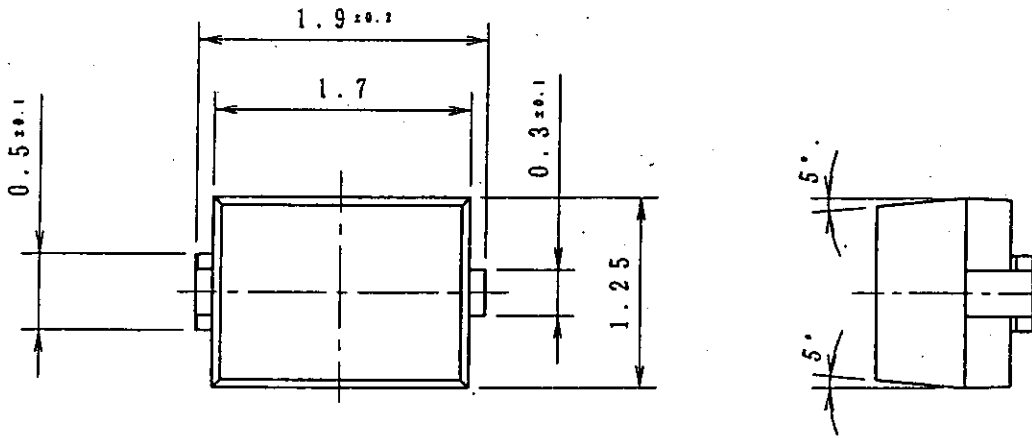


Nov. 27. 1996

Approved <i>N. Yamashita</i>	Checked <i>T. Shikida</i>	Designed <i>T. Tabata</i>
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DEVELOPMENT SPECIFICATION
(OUTLINE)

P/N:



(NOTE)

1. Unit:mm
2. Tolerance unless specified is ± 0.2 .
3. Measurement of the package doesn't include gate projection.
4. Corner of the package is R 0.2max.
5. Projection's tolerance of the package is 0.2max.

Nov. 27. 1996